

Erratum: “Spatially resolved study of quantum efficiency droop in InGaN light-emitting diodes,” [Appl. Phys. Lett. 101, 252103 (2012)]

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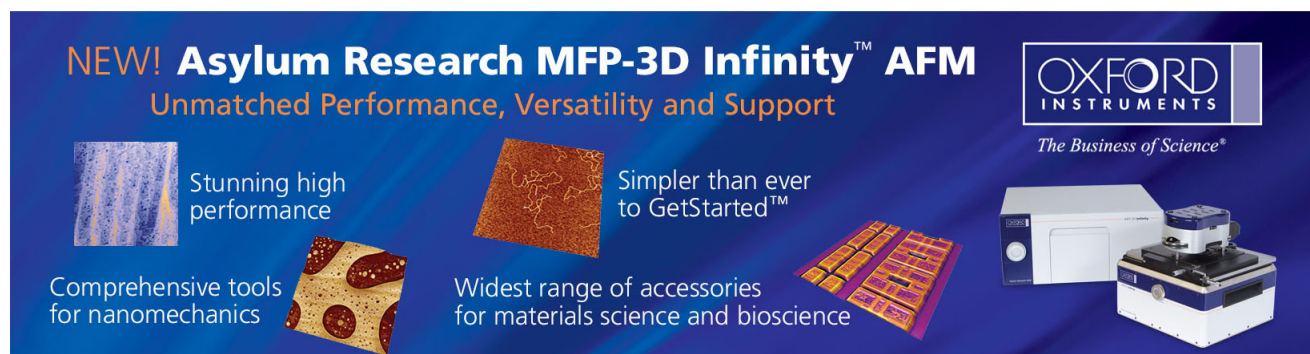
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Erratum: “Spatially resolved study of quantum efficiency droop in InGaN light-emitting diodes,” [Appl. Phys. Lett. 101, 252103 (2012)]

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The two legends in Figure 1, “type I” and “type II,” are reversed in the originally published version.¹ The corrected version is showed in Fig. 1 herein.

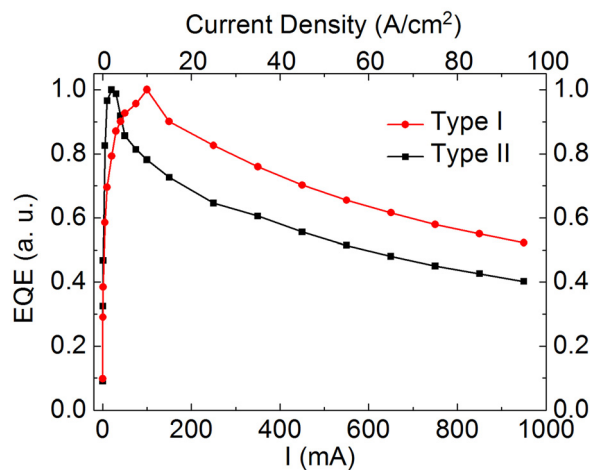


FIG. 1. Two distinctly different types of droop behaviors observed in InGaN QW LEDs.

¹Y. Lin, Y. Zhang, Z. Liu, L. Su, J. Zhang, T. Wei, and Z. Chen, *Appl. Phys. Lett.* **101**, 252103 (2012).

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